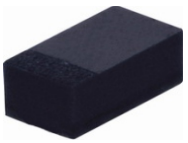
SMD Schottky Barrier Diode

COMCHIP
SMD Diodes Specialist

CDBUR0145(RoHs Device)

Io = 100 mA
VR = 45 Volts



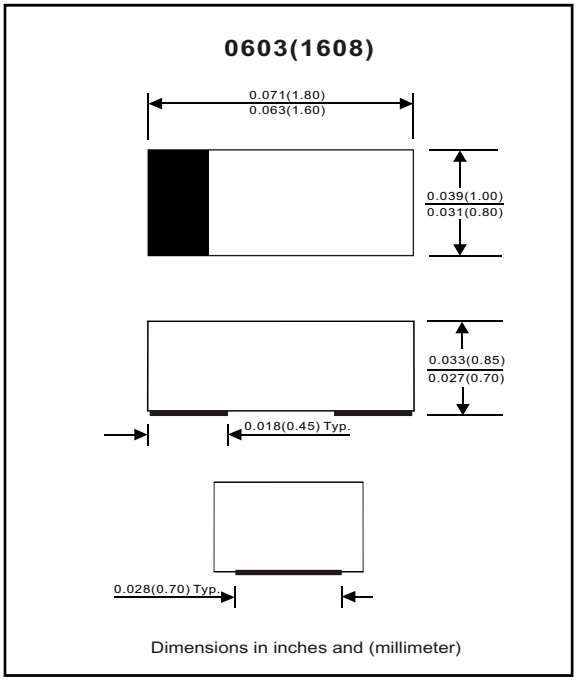
Features

Designed for mounting on small surface.

Extremely thin/leadless package.

Low leakage current.
(IR=0.1uA typ.@VR=10V)

Majority carrier conduction.



Mechanical data

Case: 0603(1608) standard package,
molded plastic.

Terminals: Gold plated, solderable per
MIL-STD-750,method 2026.

Polarity: Indicated by cathode band.

Mounting position: Any

Weight: 0.003 gram(approx.).

Maximum Rating (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Repetitive peak reverse voltage		VRRM			50	V
Reverse voltage		VR			45	V
Average forward current		Io			100	mA
Forward current,surge peak	8.3 ms single half sine-wave superimposed on rate load(JEDEC method)	IFSM		1000		mA
Power Dissipation		PD			150	mW
Sunction temperature		TSTG	-40		+125	°C
Junction temperature		Tj			+125	°C

Electrical Characteristics (at TA=25°C unless otherwise noted)

Parameter	Conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	IF = 100 mA DC	VF			0.55	V
Reverse current	VR = 10V	IR			1	uA
Capacitance between terimnals	F = 1 MHZ and 10 VDC reverse voltage	CT		9		pF

RATING AND CHARACTERISTIC CURVES (CDBUR0145)

Fig. 1 - Forward characteristics

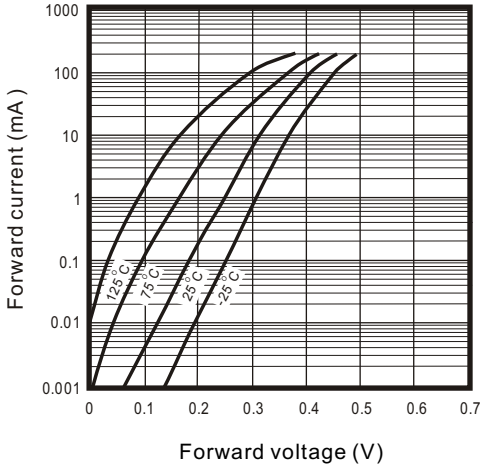


Fig. 2 - Reverse characteristics

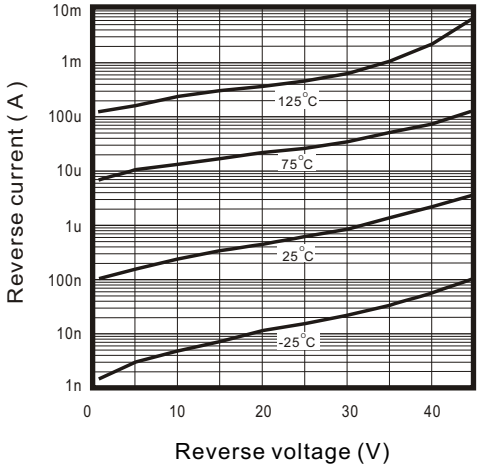


Fig.3 - Capacitance between terminals characteristics

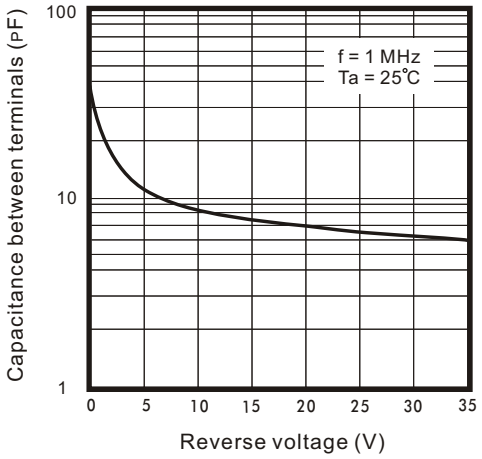


Fig.4 - Current derating curve